# Single and Quad Low Voltage, Rail-to-Rail Operational Amplifiers

The LMV821 and LMV824 are operational amplifiers with low input voltage offset and drift vs. temperature. In spite of low quiescent current requirements these devices have 5 MHz bandwidth and 1.4 V/ $\mu$ s slew rate. In addition they provide rail–to–rail output swing into 600  $\Omega$  loads. The input common–mode voltage range includes ground, and the maximum input offset voltage is only 3.5 mV. Substantially large capacitive loads can be driven by simply adding a pullup resistor or isolation resistor.

The LMV821 (single) is available in a space–saving SC70–5 while the quad comes in SOIC and TSSOP packages.

#### **Features**

Low Offset Voltage: 3.5 mV
Very low Offset Drift: 1.0 μV/°C

• High Bandwidth: 5 MHz

 $\bullet\;$  Rail–to–Rail Output Swing into a 600  $\Omega$  load

• Capable of driving highly capacitive loads

• Small Packages:

LMV821 in SC-70 LMV824 in SOIC-14 and TSSOP-14

• These Devices are Pb-Free and are RoHS Compliant

# **Typical Applications**

- Notebook Computers
- PDAs
- Modem Transmitter/ Receivers

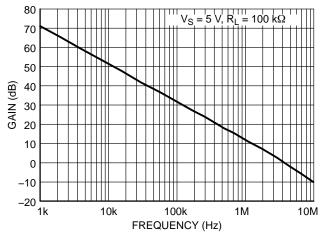


Figure 1. Gain vs. Frequency



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#### ORDERING AND MARKING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 2 of this data sheet.

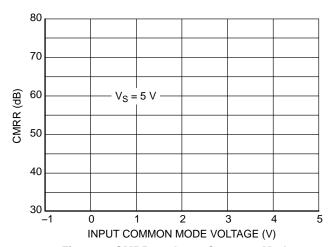
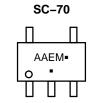


Figure 2. CMRR vs. Input Common Mode Voltage

#### **MARKING DIAGRAMS**

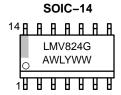


AAE = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)



LMV824 = Specific Device Code

A = Assembly Location

WL = Wafer Lot Y = Year

WW = Work Week

G = Pb-Free Package

LMV824 = Specific Device Code

A = Assembly Location

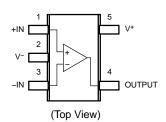
L = Wafer Lot Y = Year W = Work Week

= Pb-Free Package

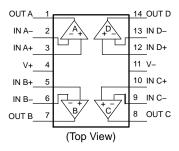
(Note: Microdot may be in either location)

#### **PIN CONNECTIONS**

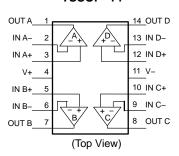
#### SC70-5



# SOIC-14



# TSSOP-14



# **ORDERING INFORMATION**

Order Number	Number of Channels	Specific Device Marking	Package Type	Shipping <sup>†</sup>
LMV821SQ3T2G	Single	AAE	SC-70 (Pb-Free)	3000 / Tape & Reel
LMV824DR2G	Quad	LMV824	SOIC-14 (Pb-Free)	2500 / Tape & Reel
LMV824DTBR2G	Quad	LMV 824	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **MAXIMUM RATINGS**

Symbol	Rating	Value	Unit
Vs	Supply Voltage (Operating Range V <sub>S</sub> = 2.7 V to 5.5 V)	5.5	V
$V_{IDR}$	Input Differential Voltage	± Supply Voltage	V
V <sub>ICR</sub>	Input Common Mode Voltage Range	-0.5 to (V+) +0.5	V
	Maximum Input Current	10	mA
t <sub>SO</sub>	Output Short Circuit (Note 1)	Continuous	
TJ	Maximum Junction Temperature (Operating Range –40°C to 85°C)	150	°C
$\theta_{\sf JA}$	Thermal Resistance		°C/W
	SC-70	280	
	SOIC-14	156	
	TSSOP-14	190	
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection – 20 sec)	235	°C
V <sub>ESD</sub>	ESD Tolerance Machine Model Human Body Model	200 2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Continuous short–circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V+ or V-will adversely affect reliability.

**2.7V DC ELECTRICAL CHARACTERISTICS** Unless otherwise noted, all min/max limits are guaranteed for  $T_A = 25$  °C,  $V_{+} = 2.7$  V,  $V_{-} = 0$  V,  $V_{CM} = V_{+}/2$ ,  $V_{0} = V_{+}/2$  and  $R_L > 1$  M $\Omega$ . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V <sub>IO</sub>			1	3.5	mV
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			4	1
Input Offset Voltage Average Drift	TCV <sub>OS</sub>			1		μV/°C
Input Bias Current	I <sub>B</sub>			105	210	nA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			315	
Input Offset Current	I <sub>IO</sub>			0.5	30	nA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			50	
Common-Mode Rejection	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 1.7 \text{ V}$	70	85		dB
Ratio		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	68			1
Power Supply Rejection Ratio	PSRR	$1.5 \text{ V} \le \text{V+} \le 4 \text{ V}, \text{ V} - = -1 \text{ V}, \text{ V}_{O} = 0 \text{ V}, \\ \text{V}_{CM} = 0.0 \text{ V}$	75	85		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			1
Input Common–Mode Voltage Range	V <sub>CM</sub>	For CMRR $\geq 53$ dB and T <sub>A</sub> = $-40^{\circ}$ C to $+85^{\circ}$ C	-0.2	-0.3 to 2.0	1.9	V
Large Signal Voltage Gain	AV	$R_L = 600 \ \Omega$ , $V_O = 0.5 \ V$ to 2.5 $V$	80	95		dB
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			1
		$R_L = 2 \text{ k}\Omega$ , $V_O = 0.5 \text{ V}$ to $2.5 \text{ V}$	83	89		1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			1
Output Swing	V <sub>OH</sub>	$R_L$ = 600 $\Omega$ to 1.35 $V$	2.5	2.58		V
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.4			1
	V <sub>OL</sub>	$R_L$ = 600 $\Omega$ to 1.35 $V$		0.13	0.21	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.3	1
	V <sub>OH</sub>	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$	2.6	2.66		1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.5			1
	V <sub>OL</sub>	$R_L = 2 \text{ k}\Omega \text{ to } 1.35 \text{ V}$		0.08	0.12	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.2	1
Output Current	I <sub>O</sub>	Sourcing, V <sub>O</sub> = 0 V	12			mA
		Sinking, $V_0 = 2.7 \text{ V}$	12	26		1
Supply Current	I <sub>CC</sub>	LMV821 (Single)		0.242	0.3	mA
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.5	1
		LMV824 (All Four Channels)		1	1.3	1
		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			1.5	1

**2.5V DC ELECTRICAL CHARACTERISTICS** Unless otherwise noted, all min/max limits are guaranteed for  $T_A = 25^{\circ}C$ ,  $V_{+} = 2.5$  V,  $V_{-} = 0$  V,  $V_{CM} = V_{+}/2$ ,  $V_{-} = V_{+}/2$  and  $R_{L} > 1$  M $\Omega$ . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V <sub>IO</sub>	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		1	3.5	mV
					4	
Output Swing	V <sub>OH</sub>	$R_L$ = 600 $\Omega$ to 1.25 V	2.3	2.37		V
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.2			1
	V <sub>OL</sub>	$R_L$ = 600 $\Omega$ to 1.25 V		0.13	0.20	1
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.3	1
	V <sub>OH</sub>	$R_L = 2 \text{ k}\Omega \text{ to } 1.25 \text{ V}$	2.4	2.46		
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	2.3			1
	V <sub>OL</sub>	$R_L = 2 \text{ k}\Omega \text{ to } 1.25 \text{ V}$		0.08	0.12	
		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			0.20	1

**2.7V AC ELECTRICAL CHARACTERISTICS** Unless otherwise specified, all limits are guaranteed for  $T_A = 25^{\circ}C$ ,  $V_{+} = 2.7$  V,  $V_{-} = 0$  V,  $V_{CM} = 1.0$  V,  $V_{O} = V_{+}/2$  and  $R_{L} > 1$  M $\Omega$ . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Slew Rate	SR	(Note 2)		1.5		V/uS
Gain Bandwidth Product	GBWP			5		MHz
Phase Margin	$\theta_{m}$			55		0
Gain Margin	G <sub>m</sub>			12.9		dB
Input-Referred Voltage Noise	e <sub>n</sub>	f = 1 kHz, V <sub>CM</sub> = 1 V		12		nV/√ <del>Hz</del>
Input-Referred Current Noise	i <sub>n</sub>	f = 1kHz		0.2		pA/√ <del>Hz</del>
Total Harmonic Distortion	THD	$f$ = 1 kHz, AV = -2, $R_L$ = 10 k $\Omega$ , $V_O$ = 1.8 $V_{PP}$		0.023		%
Amplifier-to-Amplifier Isolation		(Note 3)		135		dB

<sup>2.</sup> Connected as voltage follower with input step from 0.5 V to 1.5 V. Number specified is the average of the positive and negative slew rates.

<sup>3.</sup> Input referred,  $R_L = 100 \text{ k}\Omega$  connected to V+/2. Each amp excited in turn with 1kHz to produce  $V_O = 3 \text{ V}_{PP}$ . For Supply Voltages < 3 V,  $V_O = V+$ .

**5V DC ELECTRICAL CHARACTERISTICS** Unless otherwise noted, all min/max limits are guaranteed for  $T_A = 25^{\circ}C$ ,  $V_{+} = 5$  V,  $V_{-} = 0$  V,  $V_{-} = 0$ 

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Offset Voltage	V <sub>IO</sub>			1	3.5	mV
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			4	
Input Offset Voltage Average Drift	TCV <sub>OS</sub>			1		μV/°C
Input Bias Current	I <sub>B</sub>			119	245	nA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			380	]
Input Offset Current	I <sub>IO</sub>			0.5	30	nA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			50	]
Common-Mode Rejection	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 4.0 \text{ V}$	72	90		dB
Ratio		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	70			]
Power Supply Rejection Ratio	PSRR	$1.7 \text{ V} \leq \text{V+} \leq 4 \text{ V}, \text{V} -= 1 \text{ V}, \text{V}_{O} = 0 \text{ V}, \\ \text{V}_{CM} = 0.0 \text{ V}$	75	85		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	70			]
Input Common–Mode Voltage Range	V <sub>CM</sub>	For CMRR $\geq 58$ dB and T <sub>A</sub> = $-40^{\circ}$ C to $+85^{\circ}$ C	-0.2	-0.2 to 4.3	4.2	V
Large Signal Voltage Gain	A <sub>V</sub>	$R_L = 600 \ \Omega$ , $V_O = 1.0 \ V$ to 4.0 V	87	100		dB
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	73			]
		$R_L = 2 \text{ k}\Omega$ , $V_O = 1.0 \text{ V}$ to $4.0 \text{ V}$	84	99		1
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	82			]
Output Swing	V <sub>OH</sub>	$R_L$ = 600 $\Omega$ to 2.5 $V$	4.75	4.84		V
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	4.7			]
	V <sub>OL</sub>	$R_L$ = 600 $\Omega$ to 2.5 $V$		0.17	0.33	]
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.4	]
	V <sub>OH</sub>	RL = 2 k $\Omega$ to 2.5 V	4.85	4.9		]
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	4.8			]
	V <sub>OL</sub>	$R_L = 2 \text{ k}\Omega \text{ to } 2.5 \text{ V}$		0.1	0.15	]
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.2	]
Output Current	Io	Sourcing, Vo = 0 V	20	45		mA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	10			]
		Sinking, Vo = 5 V	20	40		]
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$	15			
Supply Current	I <sub>CC</sub>			0.3	0.4	mA
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.6	1
		LMV822 (Both Applications)		0.5	0.7	
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			0.9	
		LMV824 (All Four Applications)		1	1.3	
		$T_A = -40^{\circ}C$ to $+85^{\circ}C$			1.5	1

**5V AC ELECTRICAL CHARACTERISTICS** Unless otherwise specified, all limits are guaranteed for  $T_A = 25^{\circ}C$ ,  $V_{-} = 5$  V,  $V_{-} = 0$  V,  $V_{CM}$  = 2.0 V,  $V_{O}$  = V+/2 and  $R_{L}$  > 1 M $\Omega$ . Typical specifications represent the most likely parametric norm. Min/Max specifications are guaranteed by testing, characterization, or statistical analysis.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Slew Rate	SR	(Note 4)		2		V/μS
Gain Bandwidth Product	GBWP			5.6		MHz
Phase Margin	$\theta_{m}$			63		0
Gain Margin	G <sub>m</sub>			11.7		dB
Input-Referred Voltage Noise	e <sub>n</sub>	f = 1 kHz, V <sub>CM</sub> = 1 V		11		nV/√ <del>Hz</del>
Input-Referred Current Noise	i <sub>n</sub>	f = 1 kHz		0.21		pA/√ <del>Hz</del>
Total Harmonic Distortion	THD	$f=1~kHz,~A_V=-2,~R_L=10~k\Omega$ , $V_O=4.11~VPP$		0.012		%
Amplifier-to-Amplifier Isolation		(Note 5)		135		dB

<sup>4.</sup> Connected as voltage follower with input step from 0.5 V to 3.5 V. Number specified is the average of the positive and negative slew rates. 5. Input referred,  $R_L = 100 \text{ k}\Omega$  connected to V+/2. Each amp excited in turn with 1 kHz to produce  $V_O = 3 \text{ V}_{PP}$ . (For Supply Voltages < 3 V,  $\dot{V_O} = V+$ ).

#### **TYPICAL PERFORMANCE CHARACTERISTICS**

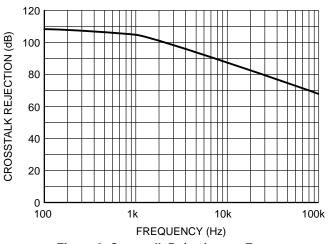


Figure 3. Crosstalk Rejection vs. Frequency

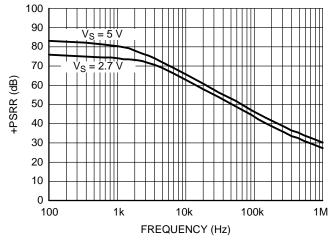


Figure 4. +PSRR vs. Frequency

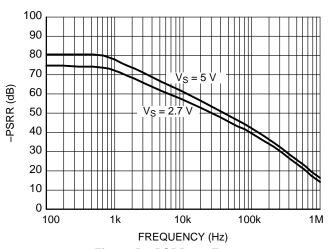


Figure 5. -PSRR vs. Frequency

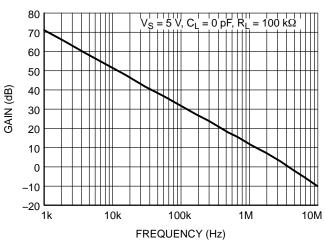


Figure 6. Gain vs. Frequency

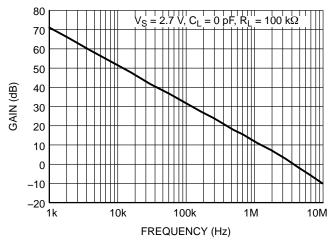


Figure 7. Gain vs. Frequency

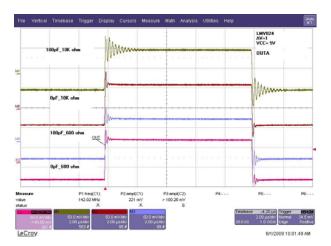


Figure 8. Non-Inverting Stability vs. Capacitive Load

# TYPICAL PERFORMANCE CHARACTERISTICS

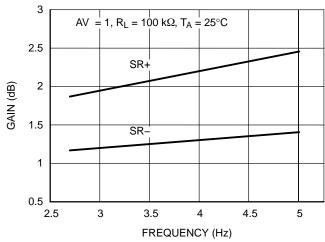


Figure 9. Gain vs. Frequency



Figure 10. Non-Inverting Large Signal Step Response



Figure 11. Non-Inverting Small Signal Step Response



Figure 12. Inverting Large Signal Step Response



Figure 13. Inverting Small Signal Step Response

#### **APPLICATIONS INFORMATION**

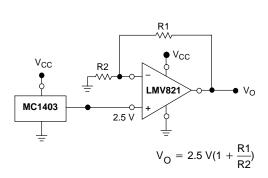


Figure 14. Voltage Reference

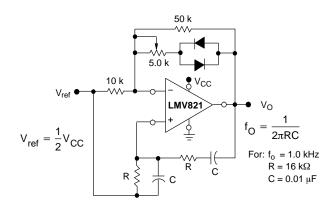


Figure 15. Wien Bridge Oscillator

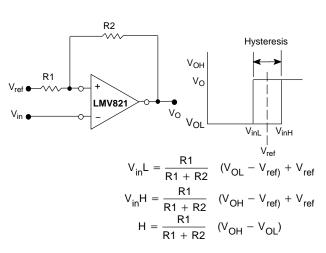
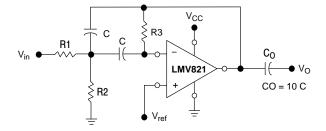


Figure 16. Comparator with Hysteresis



Given:  $f_0$  = center frequency  $A(f_0)$  = gain at center frequency

Choose value 
$$f_o$$
,  $\frac{C}{Q}$   
Then:  $R3 = \frac{R3}{\pi f_O C}$   
$$R1 = \frac{R3}{2 \, A(f_O)}$$
 
$$R2 = \frac{R1 \, R3}{4Q^2 \, R1 - R3}$$

For less than 10% error from operational amplifier,  $((Q_O f_O)/BW) < 0.1$  where  $f_O$  and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 17. Multiple Feedback Bandpass Filter



#### SC-88A (SC-70-5/SOT-353) CASE 419A-02 **ISSUE L**

**DATE 17 JAN 2013** 



- TES:
  DIMENSIONING AND TOLERANCING
  PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: INCH.
  419A-01 OBSOLETE. NEW STANDARD 3.
- 419A-02.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	0.008 REF		REF
S	0.079	0.087	2.00	2.20

# **GENERIC MARKING DIAGRAM\***



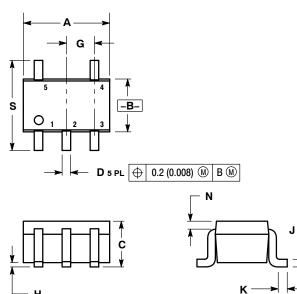
XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



# 0.50 0.0197 0.65 0.025 0.65 0.025 0.40 0.0157 1.9 mm 0.0748 SCALE 20:1

**SOLDER FOOTPRINT** 

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4

5. COLLECTOR	5. CATHODE	5. CATHODE I	5. GATE 2	5. CATHODE 4
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE 1	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	SC-88A (SC-70-5/SOT-35	63)	PAGE 1 OF 1

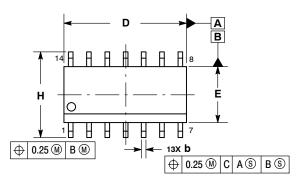
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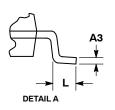


△ 0.10

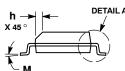
SOIC-14 NB CASE 751A-03 ISSUE L

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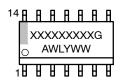




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
e	1.27	1.27 BSC		BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7 °

## **GENERIC MARKING DIAGRAM\***

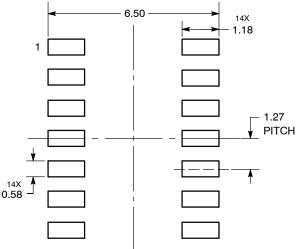


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

# **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

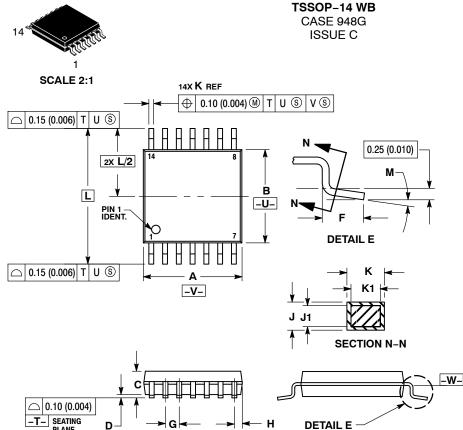
# SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	0°	8 °	0 °	8 °

# **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

<b>4</b>	7.06
1	
	<del> </del>
	0.65
, <u> </u>	<b>— — — →</b> • • • • • • • • • • • • • • • • • • •
14X	<del></del>
0.36 14X 1.26	DIMENSIONS: MILLIMETERS

**SOLDERING FOOTPRINT** 

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